

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

Claims 1 to 14: (Canceled).

15. (Currently Amended) A method for etching a pattern in an etching body in accordance with a plasma, comprising the steps of:

coupling at least temporarily a high-frequency-pulsed high-frequency power into the etching body via an at least temporarily applied high-frequency a.c. voltage; and

modulating the coupled, high-frequency-pulsed high-frequency power is modulated at a low frequency;

wherein a mark-to-space ratio of the high-frequency-pulsed high-frequency power is between 1:2 and 1:100.

16. (Previously Presented) The method of claim 15, wherein:

the etching pattern is a cut-out,

the etching body is a silicon body, and

the cut-outs are exactly defined by an etching mask in a lateral manner.

17. (Previously Presented) The method of claim 15, wherein the at least temporarily applied high-frequency a.c. voltage is provided by a high-frequency generator, the high-frequency generator generating a high-frequency carrier signal.

18. (Previously Presented) The method of claim 15, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 10 kHz to 500 kHz.

19. (Previously Presented) The method of claim 18, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 50 kHz to 200 kHz.

20. (Previously Presented) The method of claim 17, wherein the high-frequency carrier signal has a frequency of 1 MHz to 50 MHz.

21. (Currently Amended) The method of claim 20, wherein the high-frequency carrier signal has a frequency of 13.56 [[mHz]] MHz.

22. (Previously Presented) The method of claim 17, wherein the high-frequency generator generates a high-frequency power having an amplitude of 30 watts to 1200 watts.

23. (Previously Presented) The method of claim 22, wherein the high-frequency generator generates a high-frequency power having an amplitude of 50 watts to 500 watts.

24. (Previously Presented) The method of claim 15, wherein the high-frequency-pulsed high-frequency-power is coupled in the form of square-wave pulse.

25. (Currently Amended) The A method of claim 24 for etching a pattern in an etching body in accordance with a plasma, comprising the steps of:

coupling at least temporarily a high-frequency-pulsed high-frequency power into the etching body via an at least temporarily applied high-frequency a.c. voltage; and

modulating the coupled, high-frequency-pulsed high-frequency power at a low frequency,

wherein the high-frequency-pulsed high-frequency power is coupled in the form of square-wave pulses; and

wherein the square-wave pulses have a rise time of clock pulse edges of the square-wave pulses of less than 0.3  $\mu$ s.

Claim 26: (Canceled).

27. (Currently Amended) The method of claim 26 15, wherein the mark-to-space ratio of the high-frequency-pulsed high-frequency power is between 1:2 and 1:19.

28. (Previously Presented) The method of claim 15, wherein a sequence of pulses of the high-frequency-pulsed power and pulse intervals corresponds to an average high-frequency power of 1 watt to 100 watts.

29. (Previously Presented) The method of claim 15, wherein the coupled, high-frequency-pulsed high-frequency power is periodically modulated using a low-frequency clocking.

30. (Previously Presented) The method of claim 15, wherein one of a low-frequency clocking and the low-frequency modulation is performed at a frequency of 10 Hz to 10000 Hz.

31. (Previously Presented) The method of claim 30, wherein the one of the low-frequency clocking and the low-frequency modulation is performed at a frequency of 50 Hz to 1000 Hz.

32. (Previously Presented) The method of claim 15, wherein one of a low-frequency clocking and the low-frequency modulation causes the coupled, high-frequency-pulsed high-frequency power to be periodically switched on and off.

33. (Previously Presented) The method of claim 15, wherein a mark-to-space ratio of a low-frequency clocking is between 4:1 and 1:4.

34. (Previously Presented) The method of claim 33, wherein the mark-to-space ratio of the low-frequency clocking is between 1:2 and 2:1.

35. (Currently Amended) The A method of claim 15 for etching a pattern in an etching body in accordance with a plasma, comprising the steps of:

coupling at least temporarily a high-frequency-pulsed high-frequency power into the etching body via an at least temporarily applied high-frequency a.c. voltage; and

modulating the coupled, high-frequency-pulsed high-frequency power at a low frequency,

wherein a time-averaged value for the high-frequency-pulsed high-frequency power coupled into the etching body is between 1 watt and 30 watts.

36. (New) A method for etching a pattern in an etching body in accordance with a plasma, comprising the steps of:

coupling at least temporarily a high-frequency-pulsed high-frequency power into the etching body via an at least temporarily applied high-frequency a.c. voltage; and

modulating the coupled, high-frequency-pulsed high-frequency power at a low frequency;

wherein a time-averaged value for the high-frequency-pulsed high-frequency power coupled into the etching body is between 1 watt and 30 watts.

37. (New) The method of claim 36, wherein:

the etching pattern is a cut-out,

the etching body is a silicon body, and

the cut-outs are exactly defined by an etching mask in a lateral manner.

38. (New) The method of claim 36, wherein the at least temporarily applied high-frequency a.c. voltage is provided by a high-frequency generator, the high-frequency generator generating a high-frequency carrier signal.

39. (New) The method of claim 36, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 10 kHz to 500 kHz.

40. (New) The method of claim 39, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 50 kHz to 200 kHz.

41. (New) The method of claim 38, wherein the high-frequency carrier signal has a frequency of 1 MHz to 50 MHz.

42. (New) The method of claim 41, wherein the high-frequency carrier signal has a frequency of 13.56 MHz.

43. (New) The method of claim 38, wherein the high-frequency generator generates a high-frequency power having an amplitude of 30 watts to 1200 watts.

44. (New) The method of claim 43, wherein the high-frequency generator generates a high-frequency power having an amplitude of 50 watts to 500 watts.

45. (New) The method of claim 36, wherein the high-frequency-pulsed high-frequency power is coupled in the form of square-wave pulses.

46. (New) The method of claim 36, wherein a mark-to-space ratio of the high-frequency-pulsed high-frequency power is between 1:1 and 1:100.

47. (New) The method of claim 46, wherein the mark-to-space ratio of the high-frequency-pulsed high-frequency power is between 1:2 and 1:19.

48. (New) The method of claim 36, wherein a sequence of pulses of the high-frequency-pulsed power and pulse intervals corresponds to an average high-frequency power of 1 watt to 100 watts.

49. (New) The method of claim 36, wherein the coupled, high-frequency-pulsed high-frequency power is periodically modulated using a low-frequency clocking.

50. (New) The method of claim 36, wherein one of a low-frequency clocking and the low-frequency modulation is performed at a frequency of 10 Hz to 10000 Hz.

51. (New) The method of claim 50, wherein the one of the low-frequency clocking and the low-frequency modulation is performed at a frequency of 50 Hz to 1000 Hz.

52. (New) The method of claim 36, wherein one of a low-frequency clocking and the low-frequency modulation causes the coupled, high-frequency-pulsed high-frequency power to be periodically switched on and off.

53. (New) The method of claim 36, wherein a mark-to-space ratio of a low-frequency clocking is between 4:1 and 1:4.

54. (New) The method of claim 53, wherein the mark-to-space ratio of the low-frequency clocking is between 1:2 and 2:1.